

Improving The Design Process Of A MEMS-IR-Emitter

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SHORT FACTS - „CiS Forschungsinstitut“

- Research institution in Erfurt, Thuringia, Germany
- Independent - non-profit - close to business

16,5 MIO. € TOTAL OUTPUT IN 2022

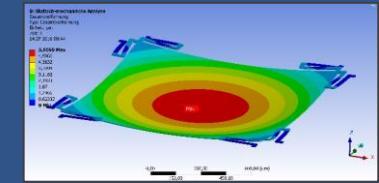
- ~120 Employees
- 52 % Public research projects
- 48 % Industrial contract research and manufacturing
- No basic funding, only project funding



→ MOEMS Development and Prototyping

**TECHNOLOGICAL EXPERTISE
In MEMS and MOEMS sensors**

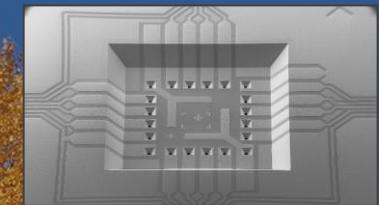
Simulation & Design



Wafer Technology & Manufacturing



Packaging & Assembly



Test & Analytics

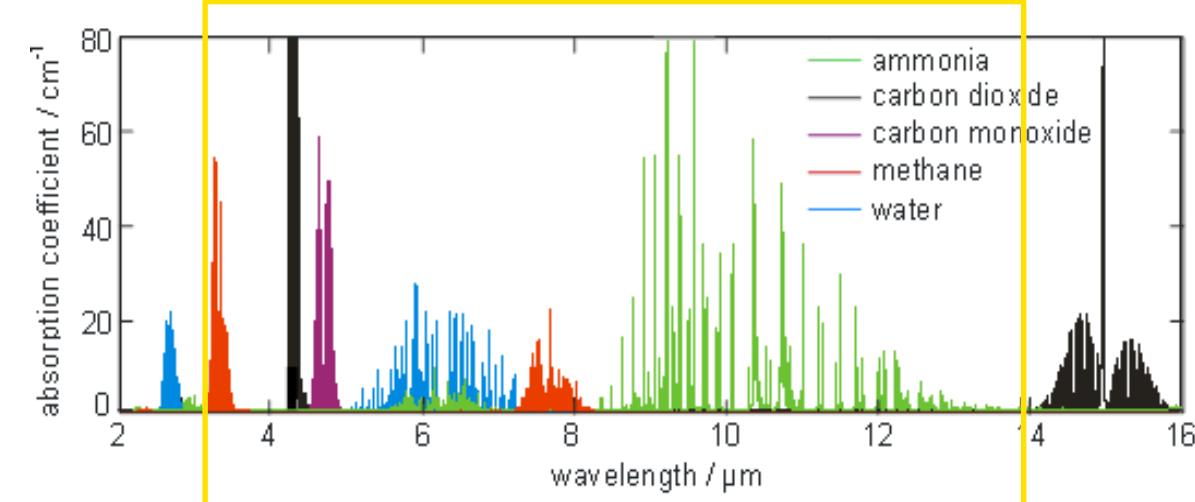
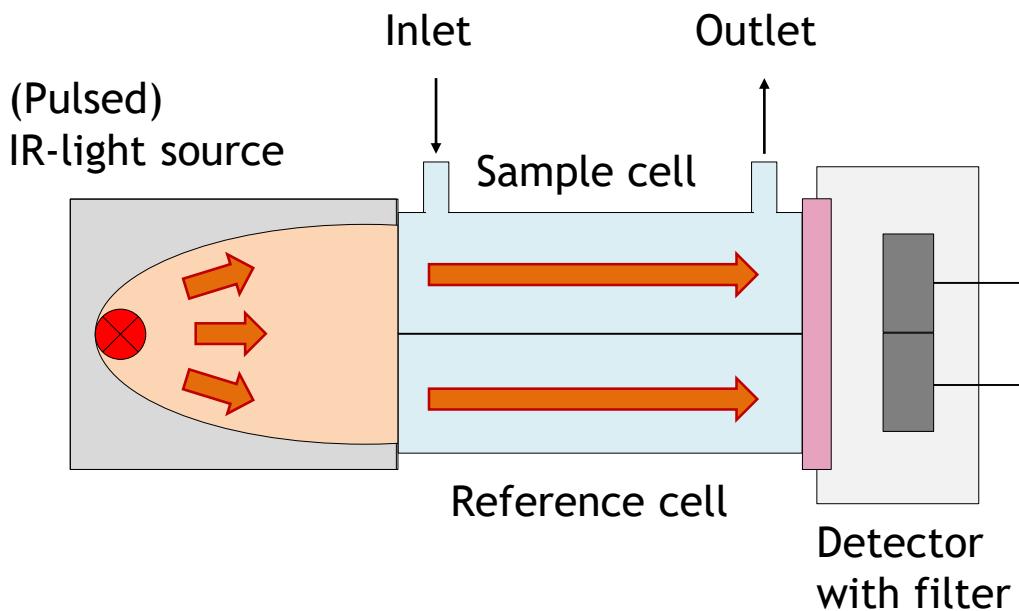


Background: IR-MEMS-Technology And Fabrication



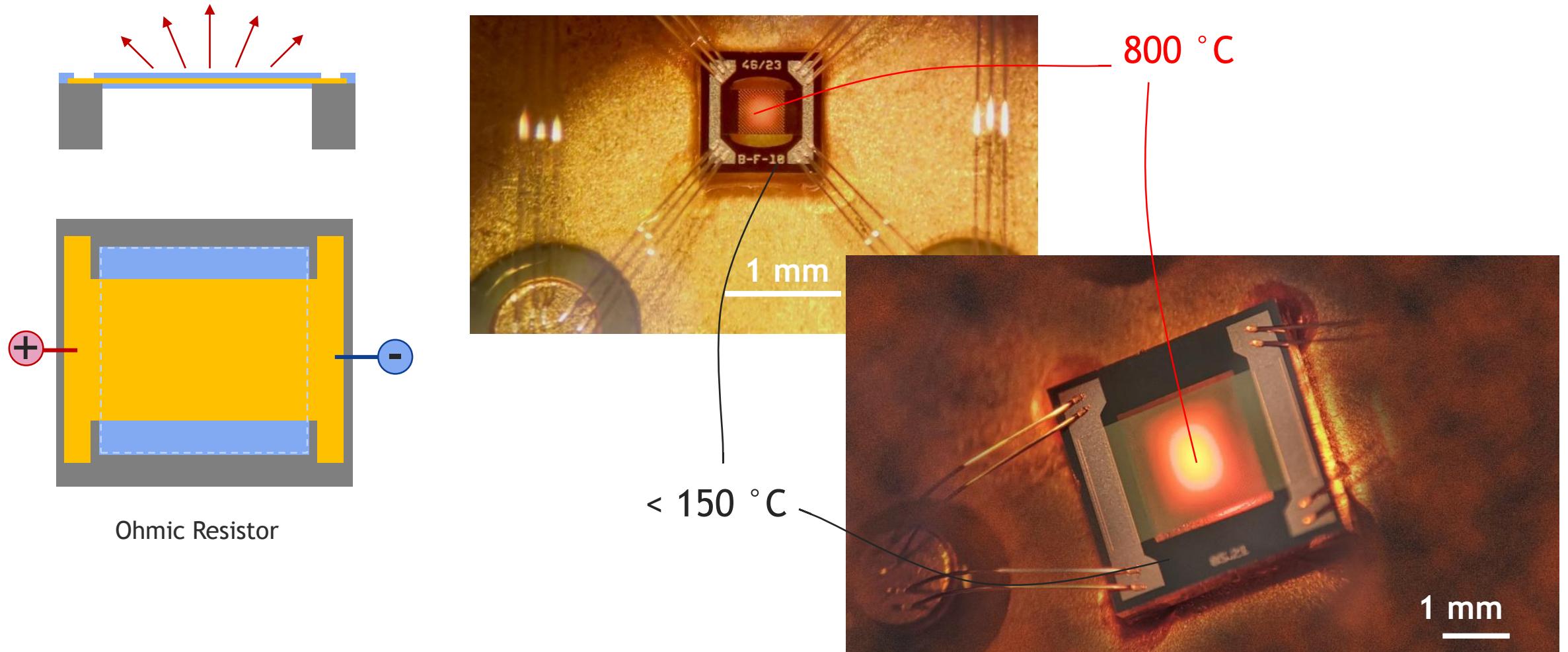
Background: IR-Emitter-Technology

Nondispersive Infrared Gassensor

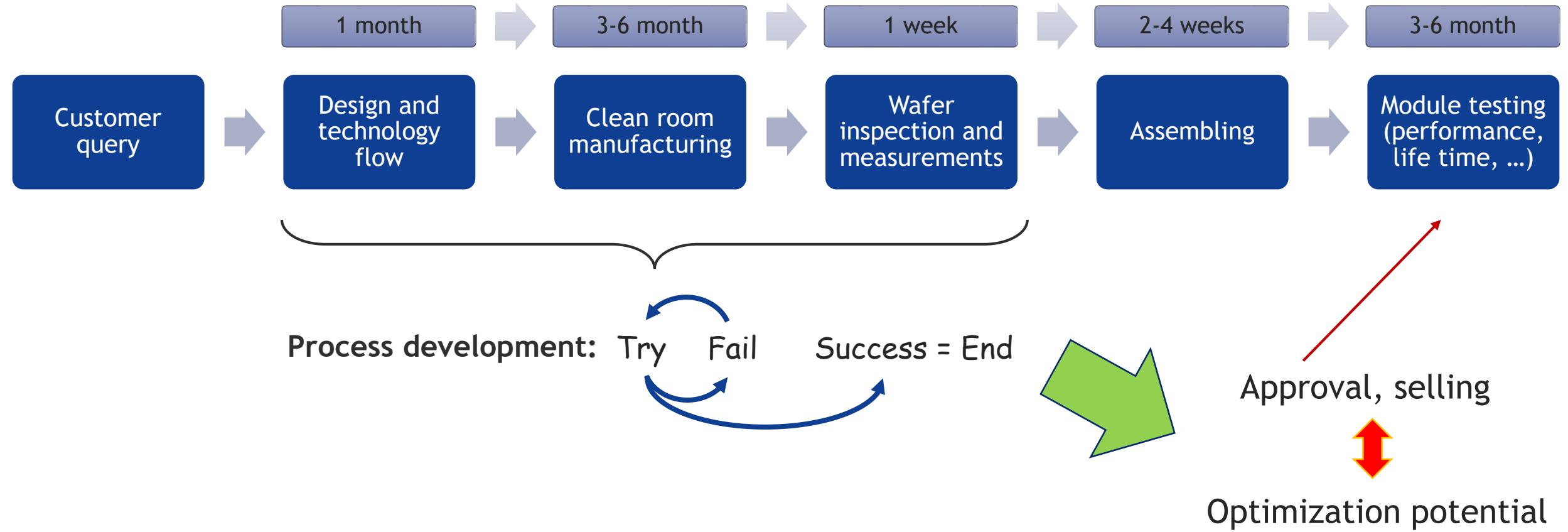


Rogalski, Antoni & Chrzanowski, K. (2014). Infrared Devices And Techniques (Revision). Metrology and Measurement Systems. 21. 10.2478/mms-2014-0057

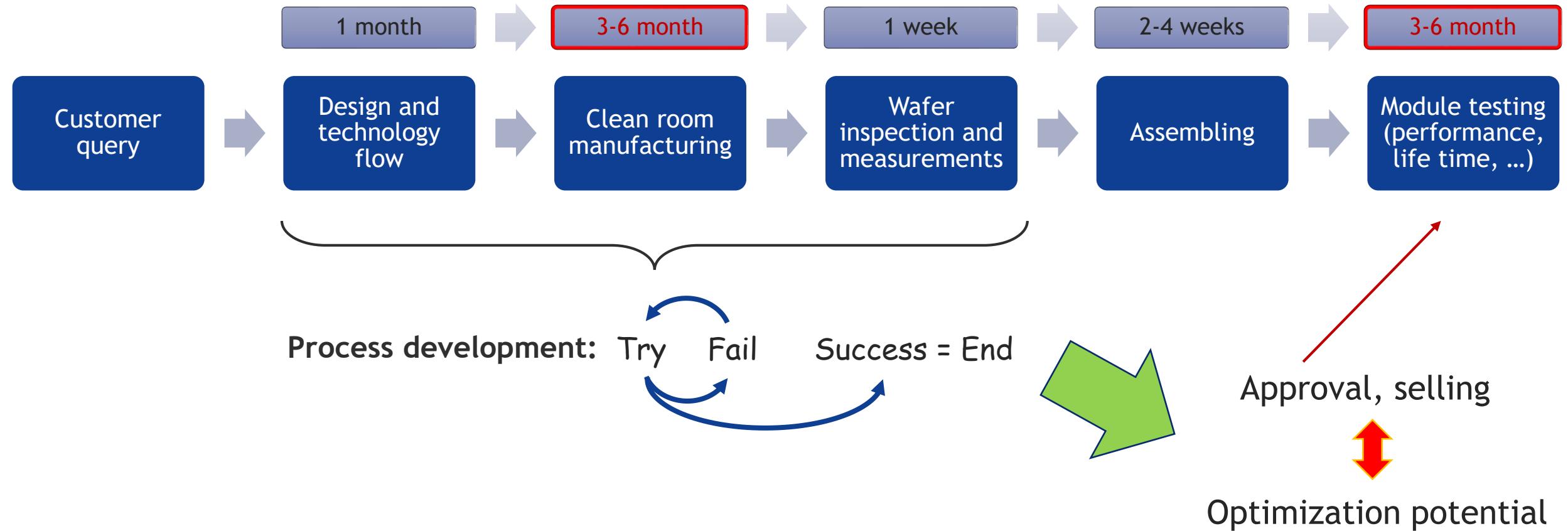
Background: IR-Emitter-Technology



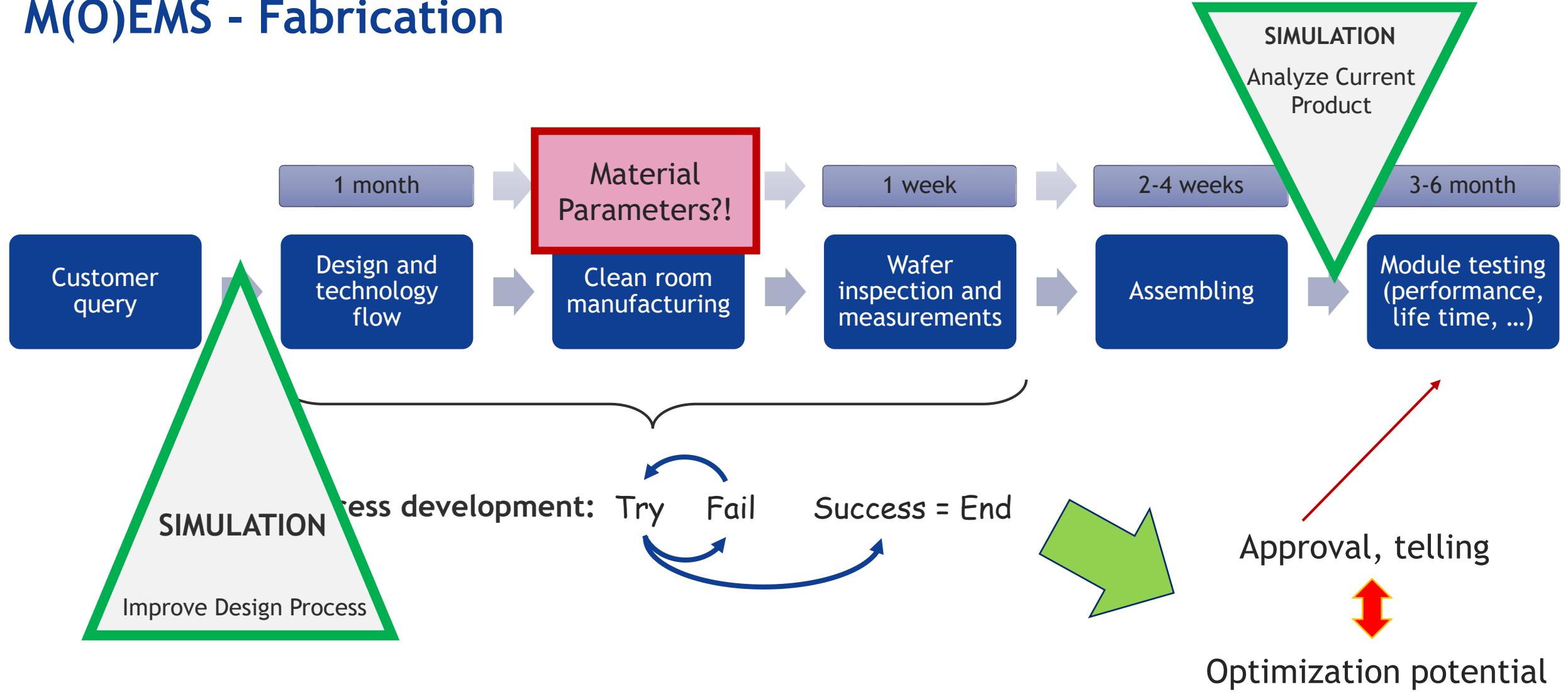
M(O)EMS - Fabrication

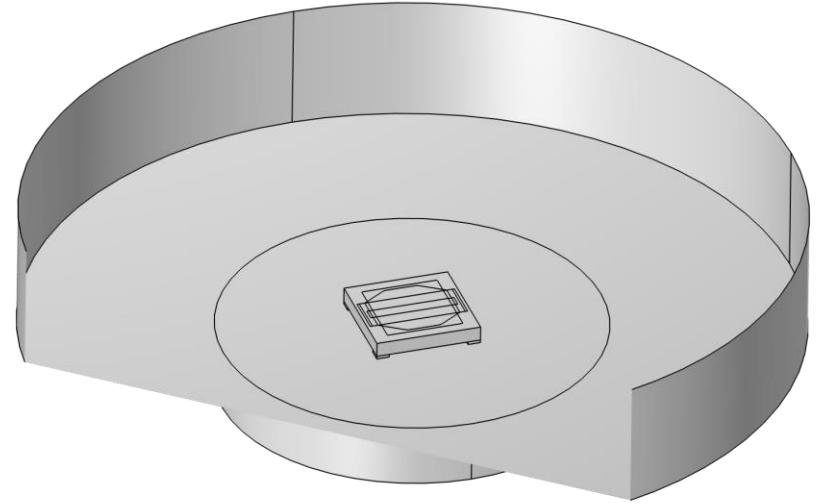


M(O)EMS - Fabrication



M(O)EMS - Fabrication



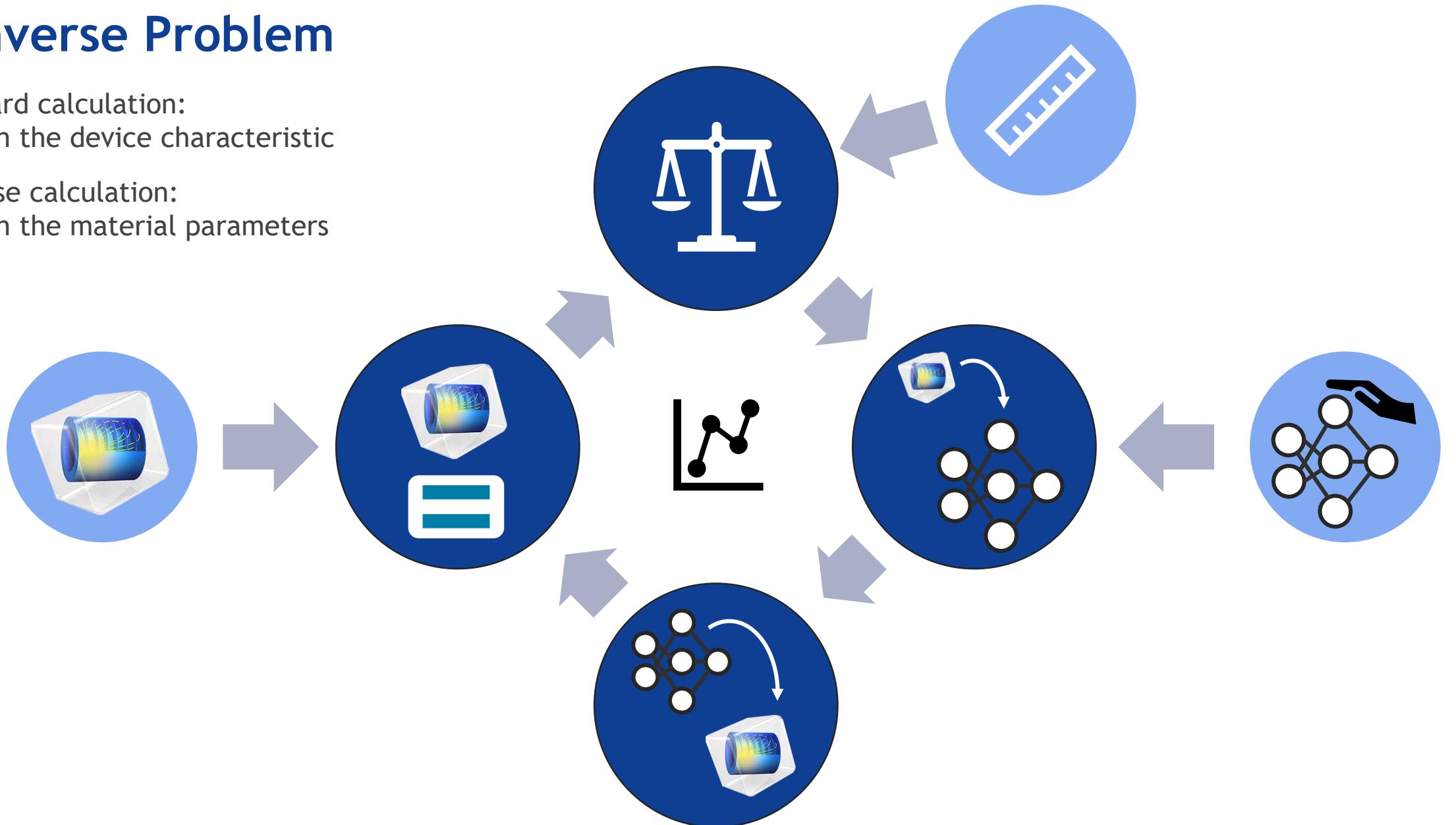


Building The Model

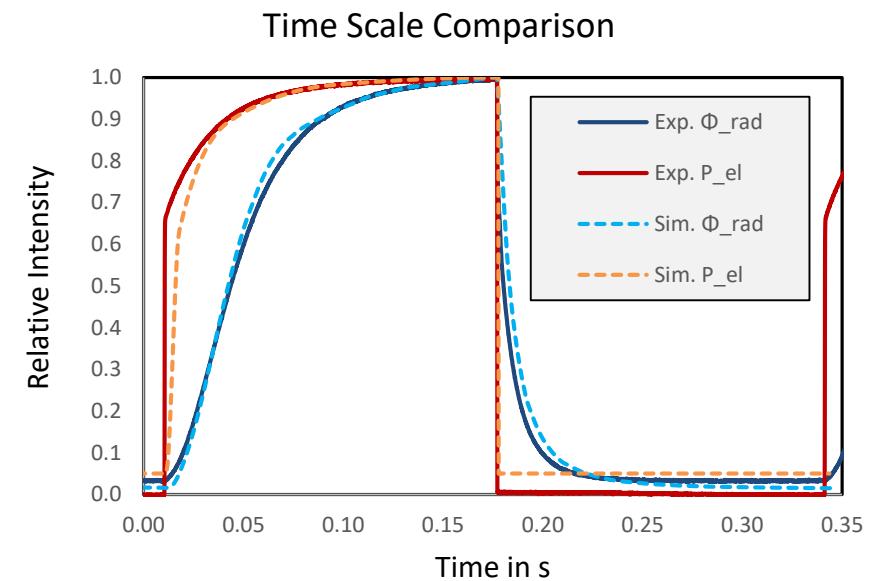
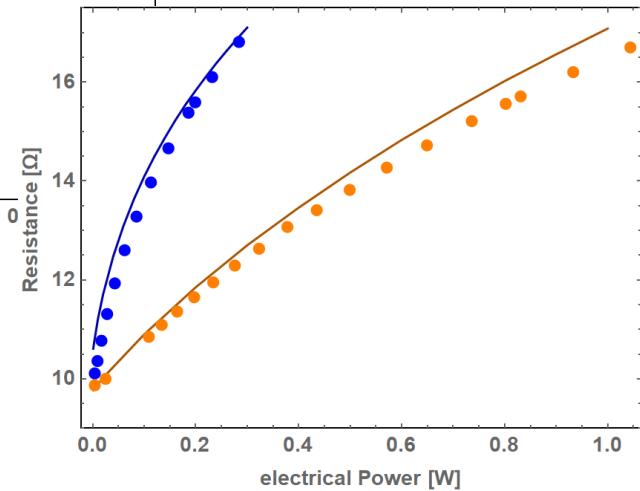
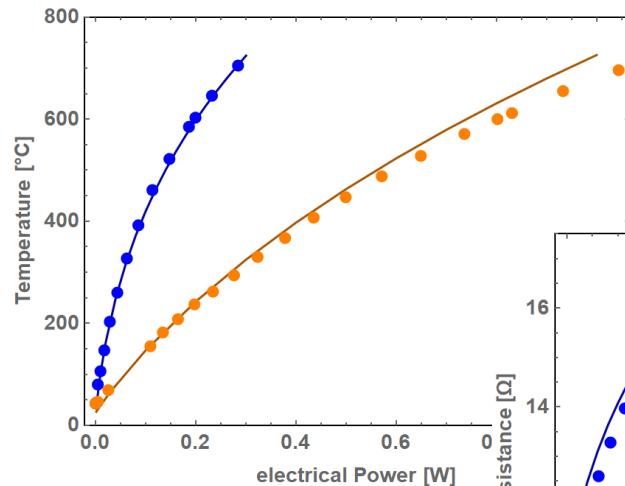
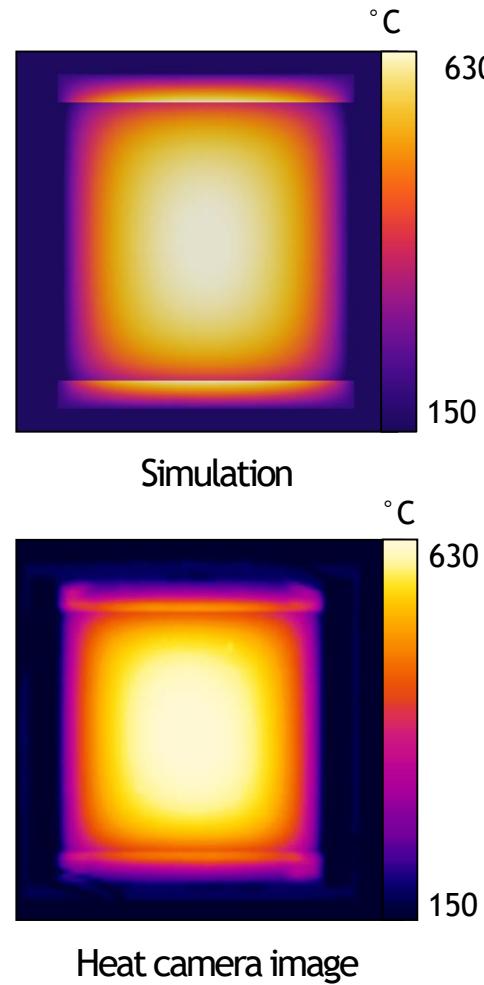
Challenge: Material Parameters Of Our Thin Layers

The Inverse Problem

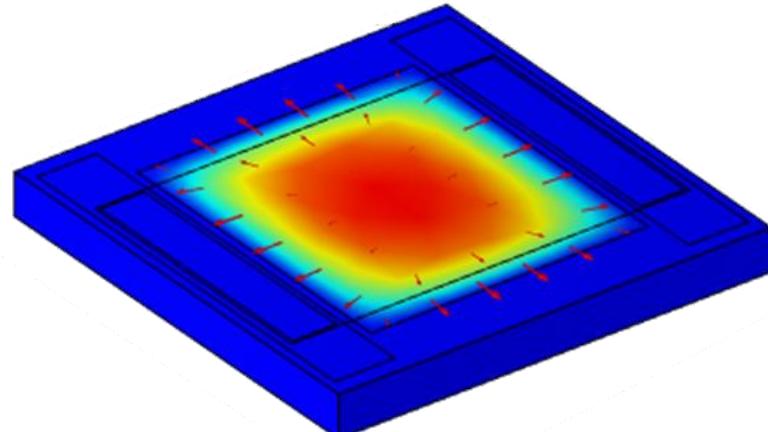
- forward calculation:
obtain the device characteristic
- inverse calculation:
obtain the material parameters



The Inverse Problem - Result

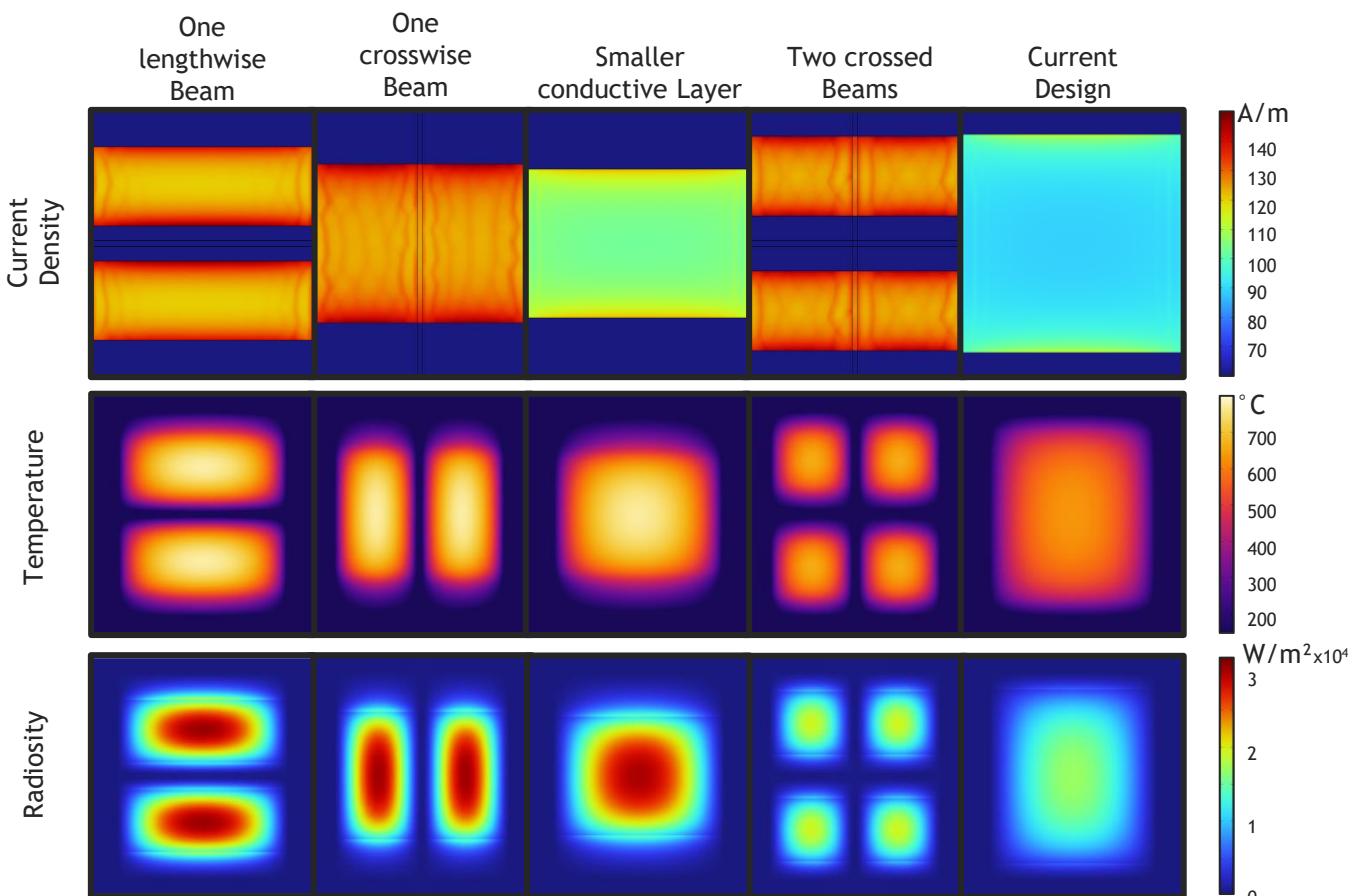
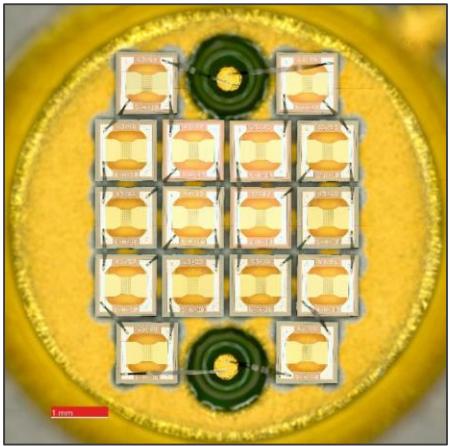


Using The Model In Design Processes



First Design Task

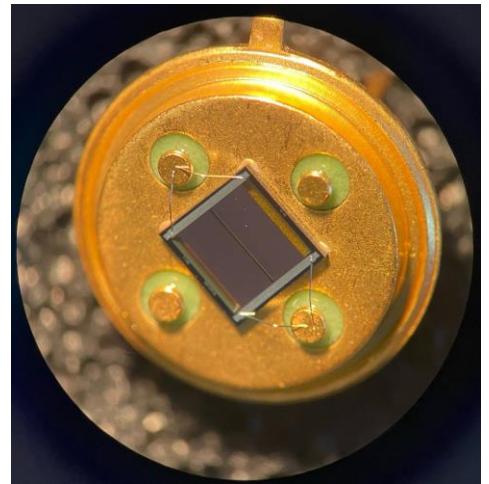
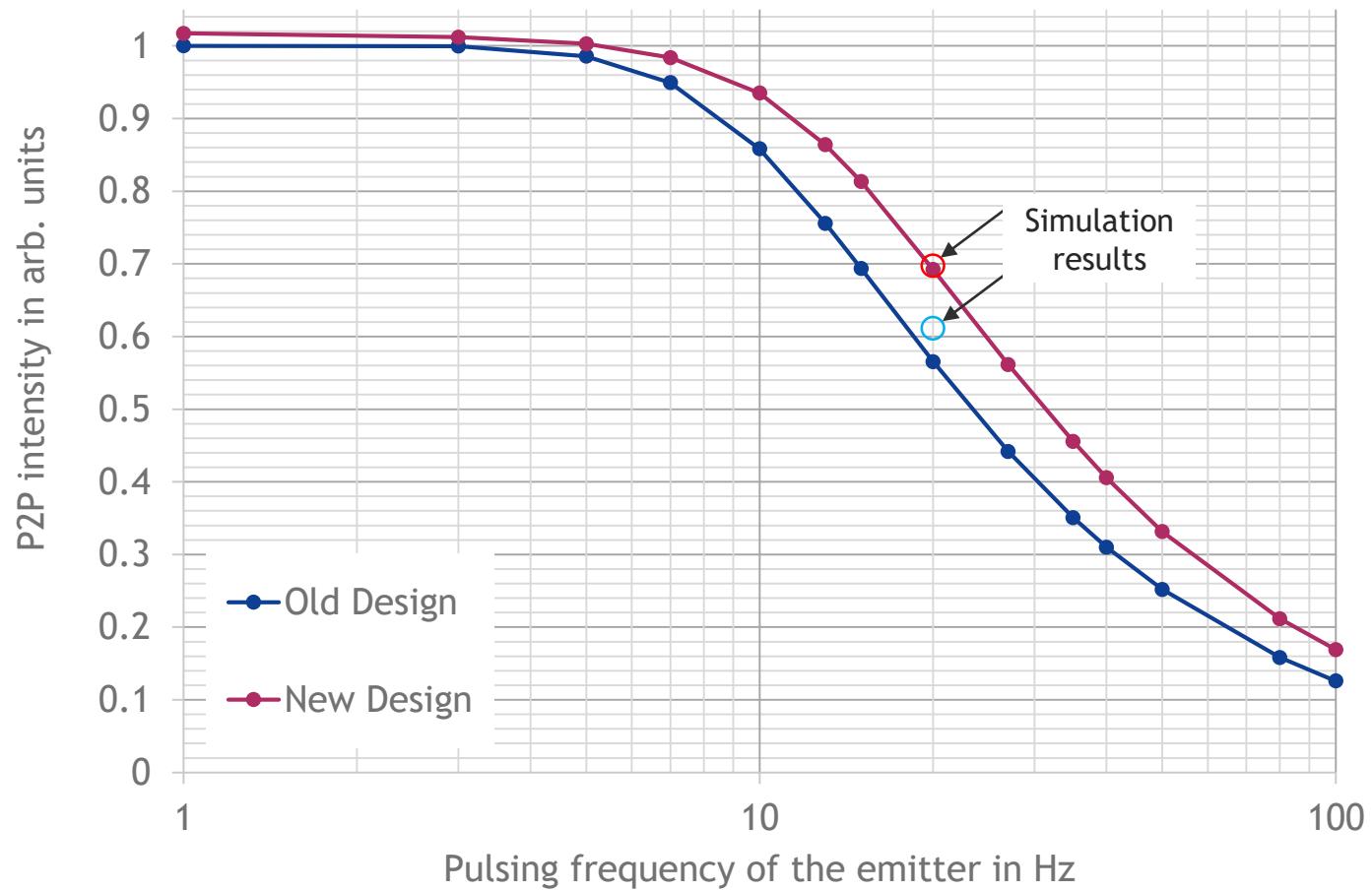
- Either bright or fast
→ Fast
- Big discrete parameter studies
→ Good prediction, what is worth to manufacture



Helping In Design

- Same life time in simulation

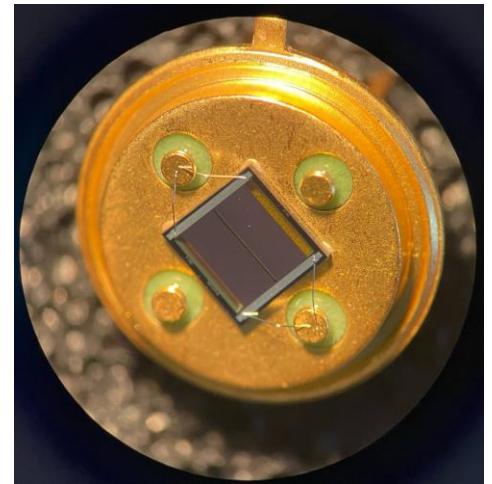
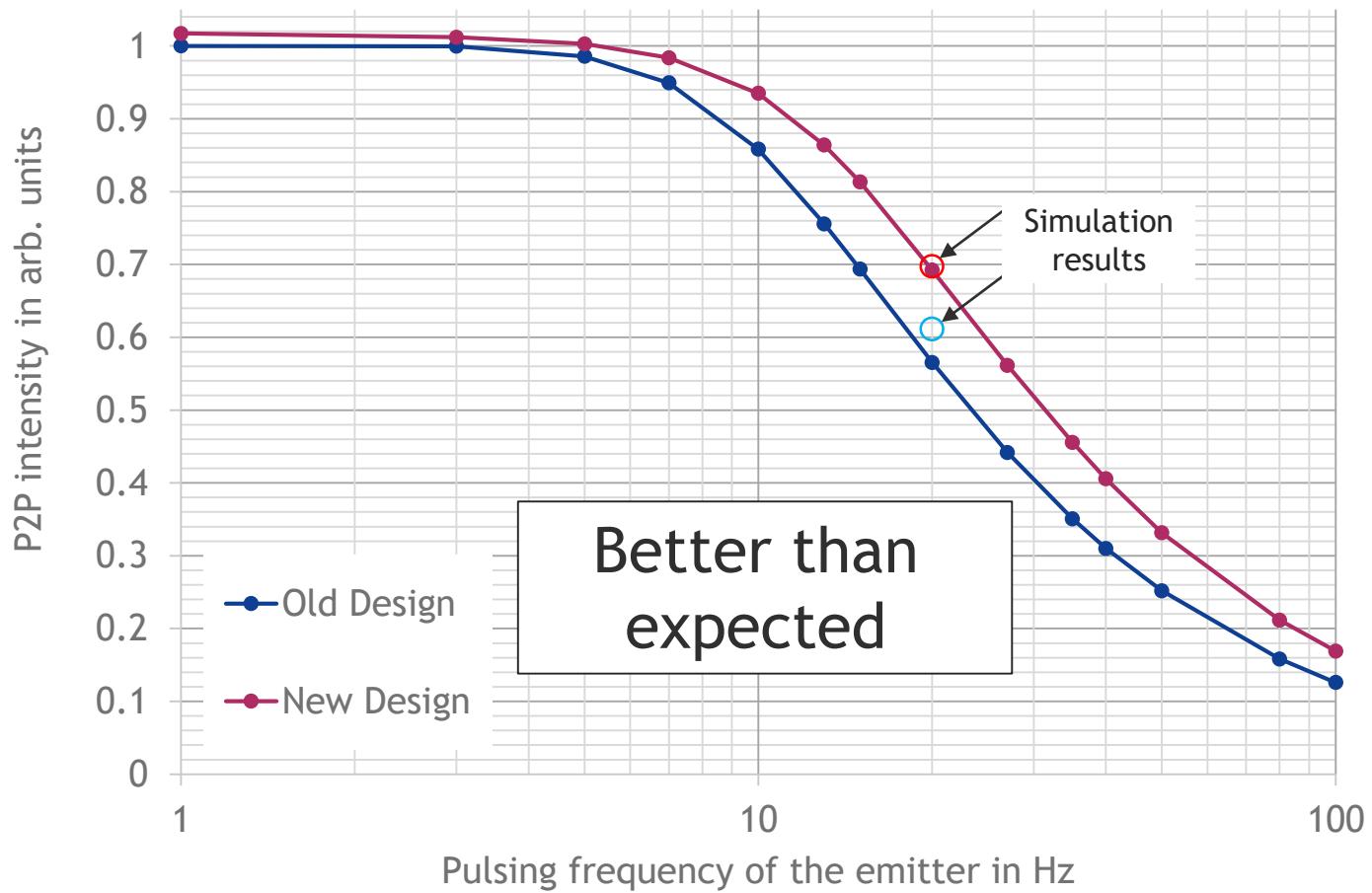
Measurements with fabricated chip



Helping In Design

- Same life time in simulation

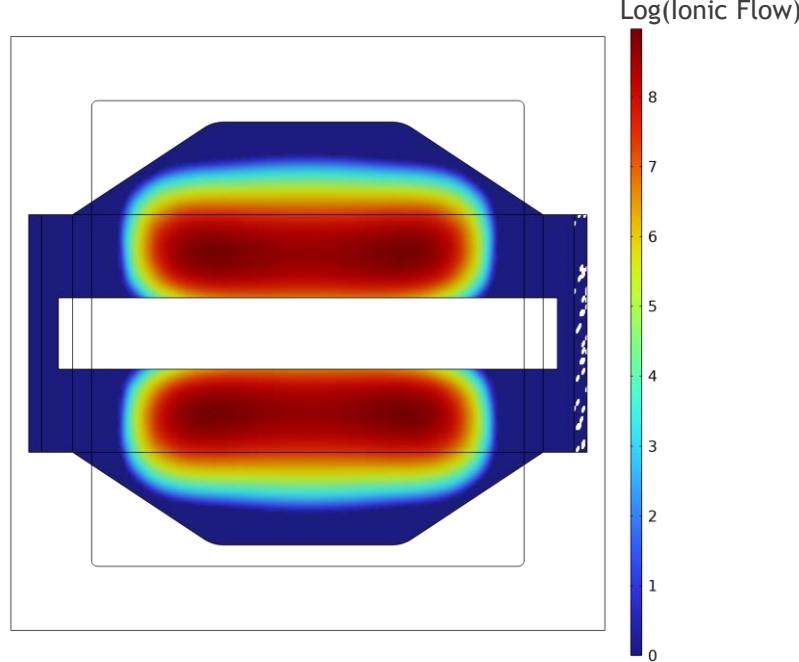
Measurements with fabricated chip



Improve Design Process With Surrogate Modelling

- 3 geometrical parameters + applied electrical power
- In parameter study only discrete combinations

→ Surrogate Modelling



Settings

Surrogate Model Training
= Compute

Label: Surrogatmodell-Training

Study Settings

Compute action: Compute and build surrogate model

Solution to use: Automatic

Surrogate model: Design of experiments (No surrogate model)

Output table group: Statistische Versuchsplanung 1 {de2}

Quantities of interest (Outputs)

| Expression | Description | Individual solution to use |
|------------|-------------|----------------------------|
| comp1.bnd2 | Tmax | From "Solution to use" |
| comp1.bnd1 | EMigr | From "Solution to use" |
| comp1.var1 | Radiation | From "Solution to use" |

Input Parameters

| Parameter | Source type | Parameter description |
|-------------------------|-------------|--------------------------|
| A_dy (Abstand zur Gru | Analytic | Uniform from [30, 150] |
| A_Px (Ecken) | Analytic | Uniform from [-400, -40] |
| A_AI (Aussparung: Lär | Analytic | Uniform from [100, 400] |
| P_el (eingespeiste Leis | Analytic | Uniform from [420, 770] |

Correlation groups

Correlation matrix

Active

Input parameters sampling settings

Number of input points type: Manual

Number of input points: 1000

Random seed type: Automatic

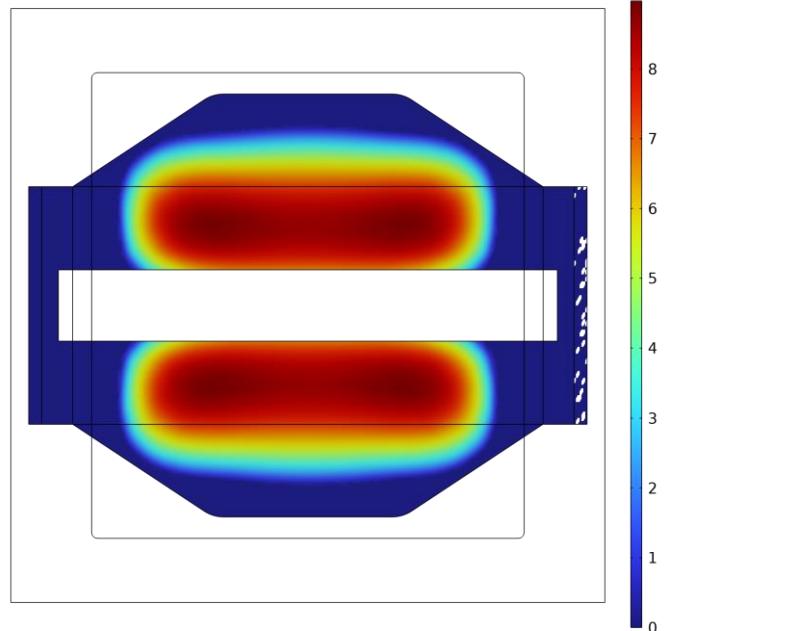
Initial random seed: 1014

Advanced Settings

Improve Design Process With Surrogate Modelling

- 3 geometrical parameters + applied electrical power
- In parameter study only discrete combinations

→ Surrogate Modelling



Settings

Deep Neural Network

Plot Create Plot Train Model Continue Training

Label: Tiefes neuronales Netzwerk 2

Layers

| Type | Settings |
|-------|--|
| Dense | Input, Input features=4, Output features=32, Activation=tanh |
| Dense | Hidden, Output features=18, Activation=tanh |
| Dense | Hidden, Output features=10, Activation=tanh |
| Dense | Hidden, Output features=6, Activation=tanh |
| Dense | Output, Output features=3, Activation=tanh |

Data

Data source: Result table

Result table: Designdaten 1 {tbl8}

Ignore NaN/Inf data points

Data Column Settings

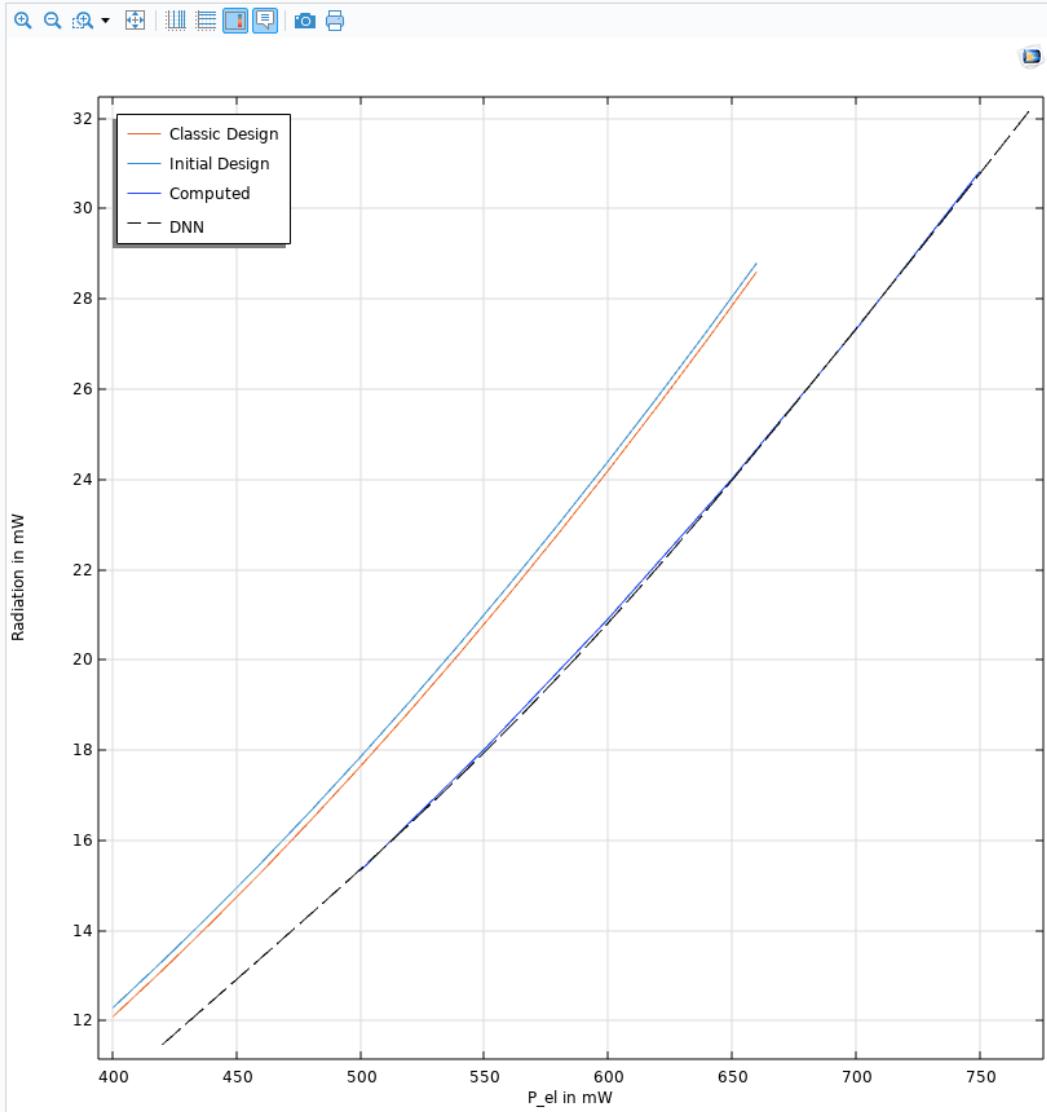
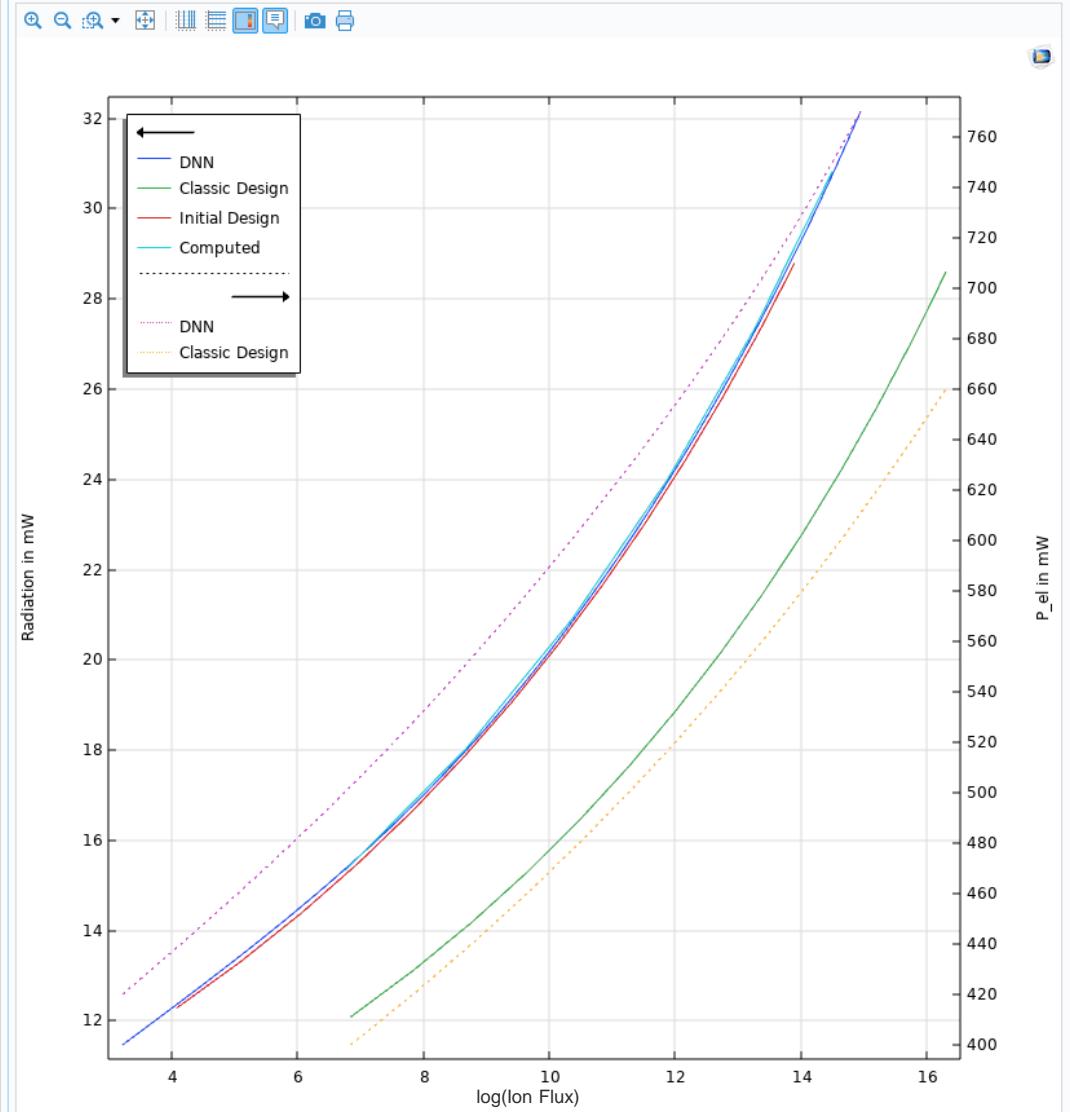
| Columns | Type | Settings |
|------------|-----------------|----------------------------|
| A_dy | Argument | Name=x1, Scaling=to01 |
| A_Px | Argument | Name=x2, Scaling=to01 |
| A_AI | Argument | Name=x3, Scaling=to01 |
| P_el | Argument | Name=x4, Scaling=to01 |
| comp1.bnd2 | Function values | Name=dnn_T, Scaling=to01 |
| comp1.bnd1 | Function values | Name=dnn_EM, Scaling=to01 |
| comp1.var1 | Function values | Name=dnn_Rad, Scaling=to01 |

Application For Better Visualization

Datei Home
Compute Haupt

Eingaben

Slit Width: 150 μm
Corner: -200 μm
Distance To Wall: 50 μm



Conclusion

- Model building of existing technology without knowing exact material parameters
- New evaluation of current designs
 - Life time prediction
- Developing new designs
 - Better preselection of design worth manufacturing
 - Surrogate Modelling allows steplessly adjustable parameters



Thank you for your attention!

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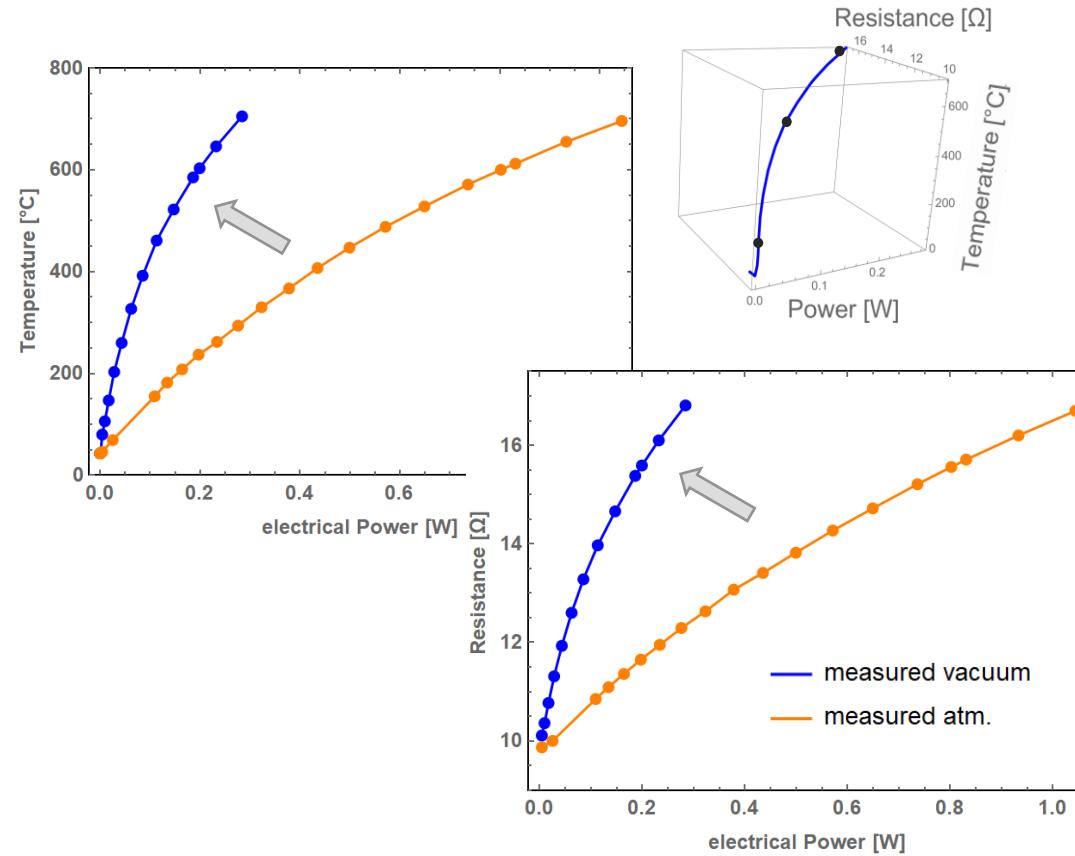
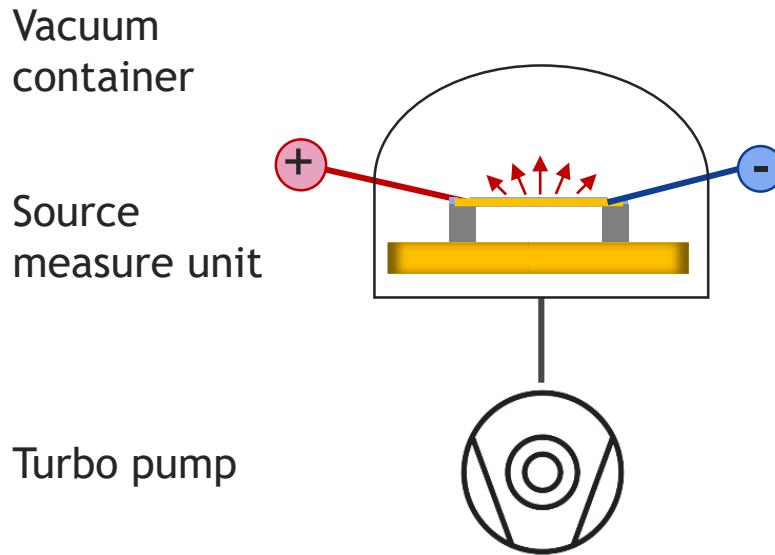
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Verification experiment

Unknown parameters:

- Temperature dependent resistance
- Temperature dependent thermal conductivity

Remove influence of thermal conduction and convection by air



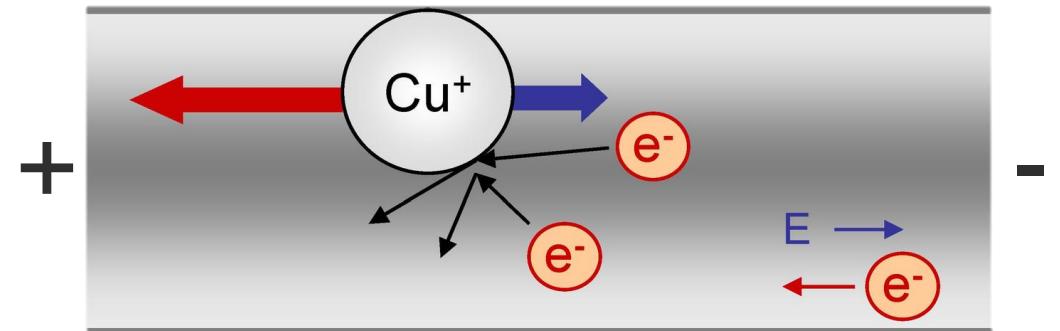
Life Time Modeling

- Dominant failure mechanism is Electromigration

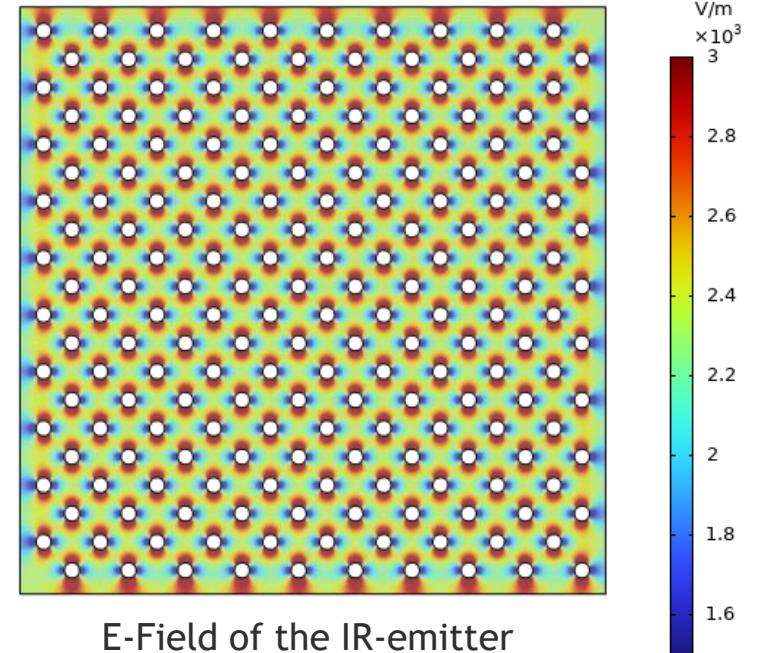
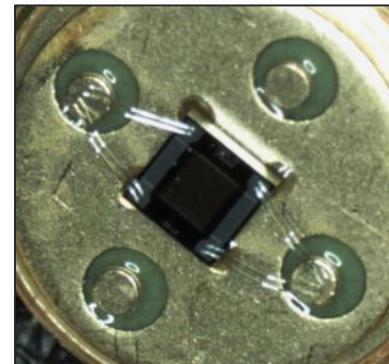
$$J_{max} = K \cdot \frac{kT}{E} \cdot \exp\left(\frac{E_A}{kT}\right)$$

- K - summarized material properties, k - Boltzmann constant, T - Temperature, E_A - Activation energy, E - Electric Field

Analyzing current design
with perforated conductive layer



<https://commons.wikimedia.org/wiki/File:Electromigration.png>
Authour: Linear 77, Source: Own work



E-Field of the IR-emitter